

N-Channel 8 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
8	0.086 at $V_{GS} = 4.5$ V	1.34 ^a	7.1
	0.093 at $V_{GS} = 2.5$ V	1.29	
	0.102 at $V_{GS} = 1.8$ V	1.23	
	0.120 at $V_{GS} = 1.5$ V	0.7	

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

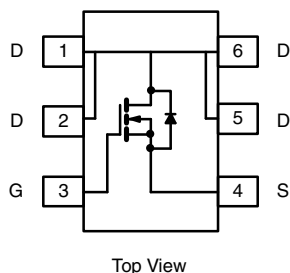


RoHS
COMPLIANT
HALOGEN
FREE

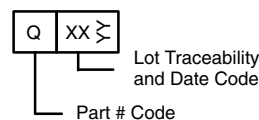
APPLICATIONS

- Load Switch for Portable Devices

SC-89 (6-LEADS)



Marking Code



Ordering Information: Si1050X-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	8	V
Gate-Source Voltage	V_{GS}	± 5	
Continuous Drain Current ($T_J = 150$ °C) ^a	$T_A = 25$ °C	I_D 1.34 ^{b, c}	A
	$T_A = 70$ °C	1.07 ^{b, c}	
Pulsed Drain Current	I_{DM}	6	
Continuous Source-Drain Diode Current	$T_A = 25$ °C	I_S 0.2 ^{b, c}	W
Maximum Power Dissipation ^a	$T_A = 25$ °C	P_D 0.236 ^{b, c}	
	$T_A = 70$ °C	0.151 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	R_{thJA}	440	530	°C/W
		540	650	

Notes:

- Based on $T_C = 25$ °C.
- Surface mounted on 1" x 1" FR4 board.
- $t = 5$ s.
- Maximum under steady state conditions is 650 °C/W.

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	8			V	
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		18.2		mV/°C	
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 2.55			
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.35		0.9	V	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 5 V			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 8 V, V _{GS} = 0 V			1	μA	
		V _{DS} = 8 V, V _{GS} = 0 V, T _J = 85 °C			10		
On-State Drain Current ^a	I _{D(on)}	V _{DS} = ≥ 5 V, V _{GS} = 4.5 V	6			A	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 1.34 A		0.071	0.086	Ω	
		V _{GS} = 2.5 V, I _D = 1.29 A		0.078	0.093		
		V _{GS} = 1.8 V, I _D = 1.23 A		0.085	0.102		
		V _{GS} = 1.5 V, I _D = 0.76 A		0.092	0.120		
Forward Transconductance	g _{fs}	V _{DS} = 4 V, I _D = 1.34 A		4.12		S	
Dynamic ^b							
Input Capacitance	C _{iss}	V _{DS} = 4 V, V _{GS} = 0 V, f = 1 MHz		585		pF	
Output Capacitance	C _{oss}			190			
Reverse Transfer Capacitance	C _{rss}			130			
Total Gate Charge	Q _g	V _{DS} = 4 V, V _{GS} = 5 V, I _D = 1.34 A		7.7	11.6	nC	
		V _{DS} = 4 V, V _{GS} = 4.5 V, I _D = 1.34 A		7.1	10.7		
					1.14		
					1.69		
Gate-Source Charge	Q _{gs}						
Gate-Drain Charge	Q _{gd}						
Gate Resistance	R _g	f = 1 MHz		3.5	4.6	Ω	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 4 V, R _L = 3.6 Ω I _D ≅ 1.1 A, V _{GEN} = 4.5 V, R _g = 1 Ω		6.8	10.2	ns	
Rise Time	t _r			35	53		
Turn-Off DelayTime	t _{d(off)}			25	37.5		
Fall Time	t _f			6	9		
Drain-Source Body Diode Characteristics							
Pulse Diode Forward Current ^a	I _{SM}				6	A	
Body Diode Voltage	V _{SD}	I _S = 1.0 A		0.8	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}	I _F = 1.0 A, di/dt = 100 A/μs		18.5	28	nC	
Body Diode Reverse Recovery Charge	Q _{rr}			3.7	5.7	ns	
Reverse Recovery Fall Time	t _a			6.7			
Reverse Recovery Rise Time	t _b			11.8			

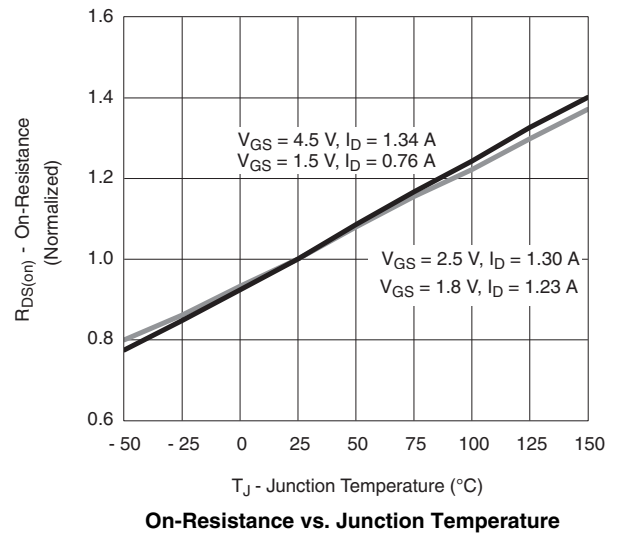
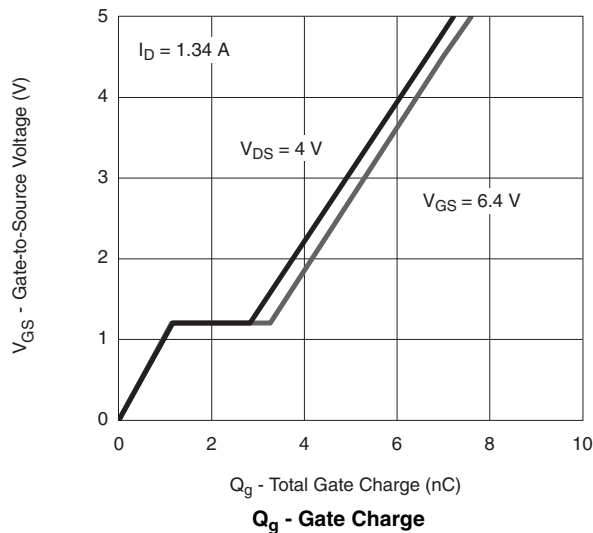
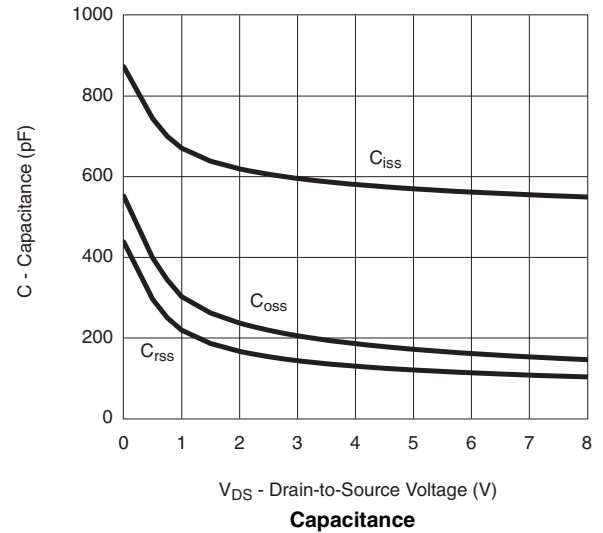
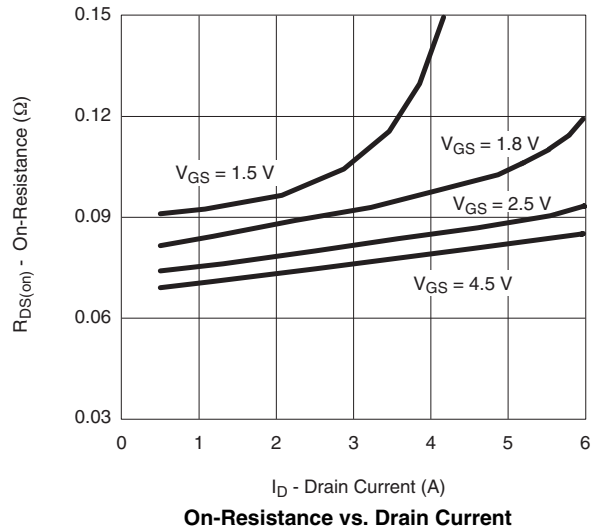
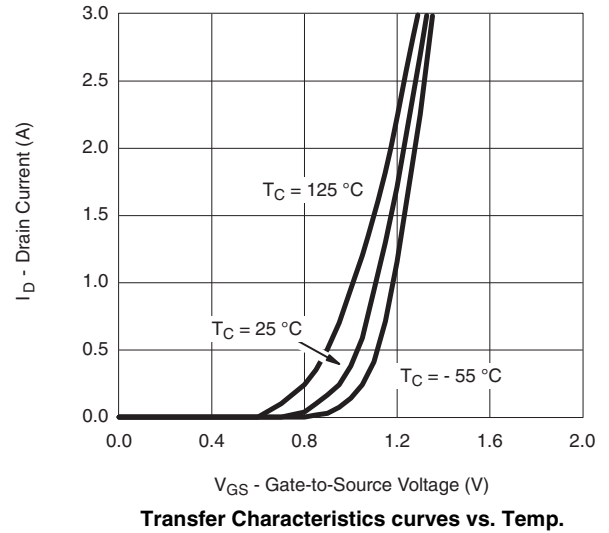
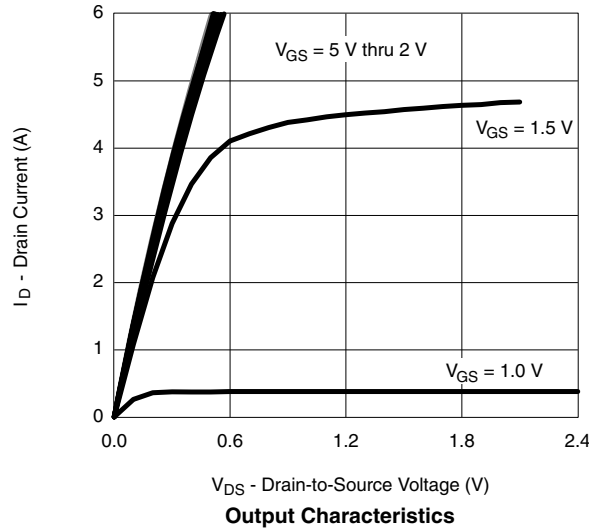
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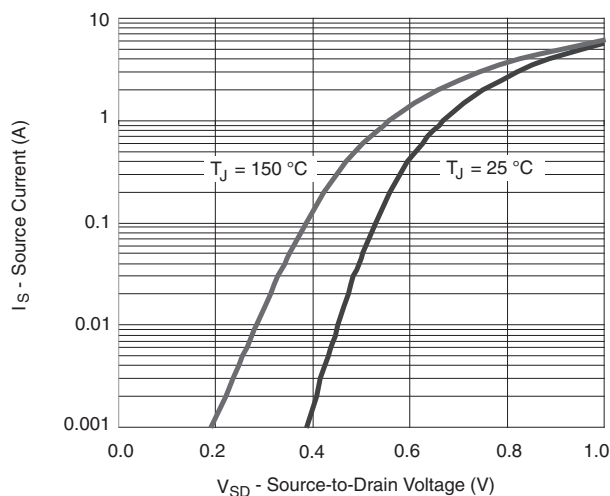
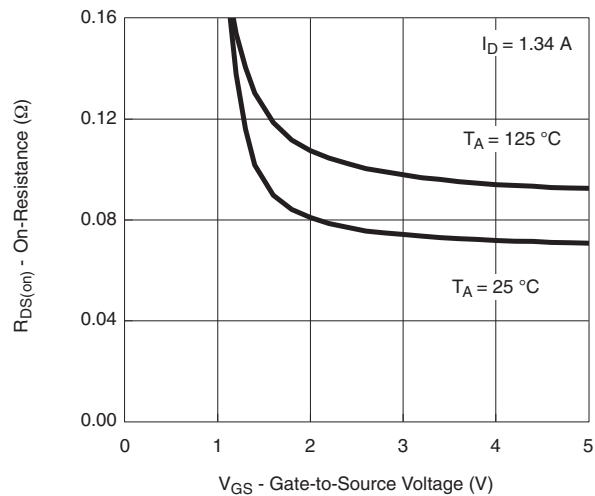
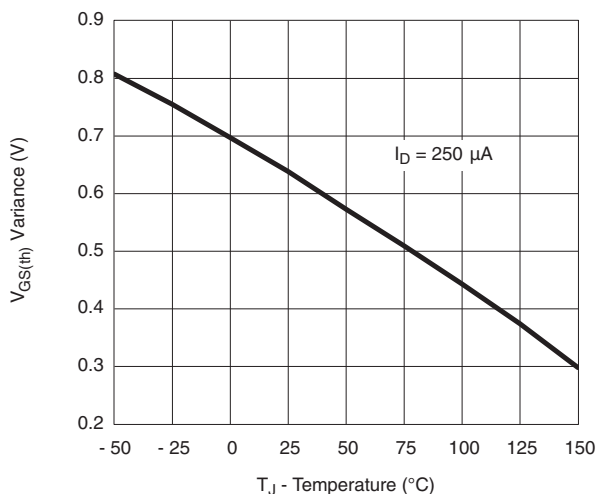
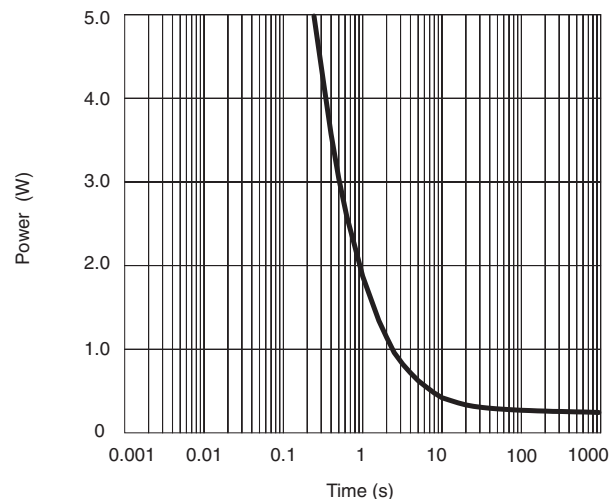
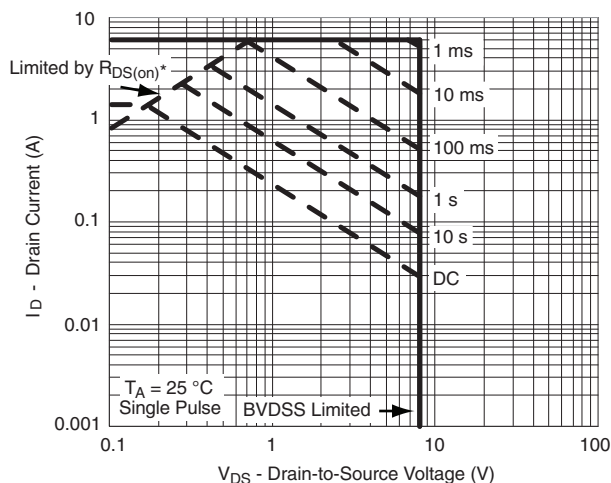
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

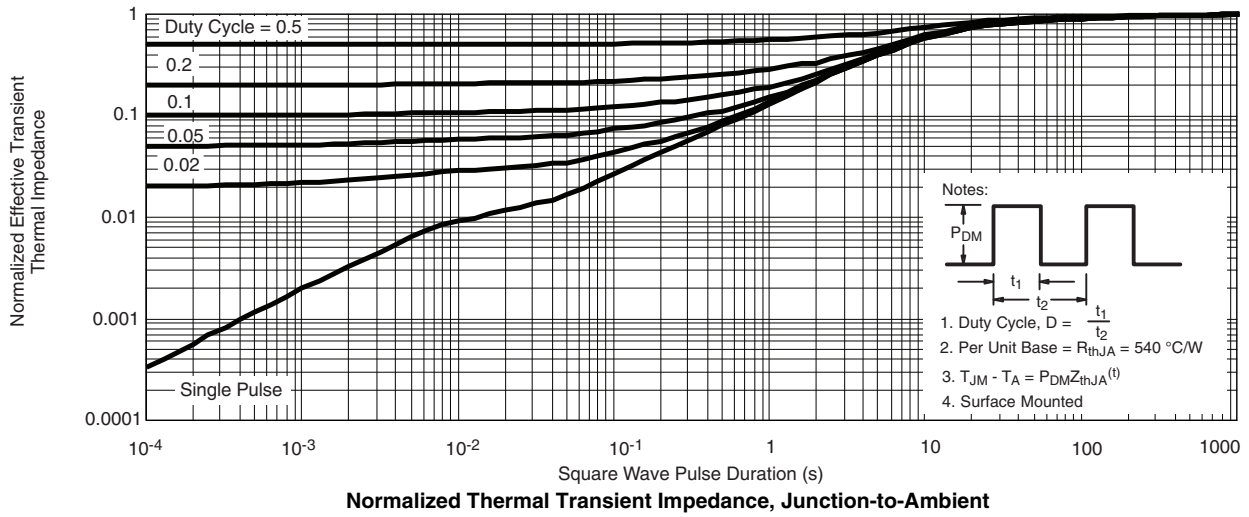


TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Source-Drain Diode Forward Voltage

 $R_{DS(on)}$ vs V_{GS} vs Temperature

Threshold Voltage

Single Pulse Power


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

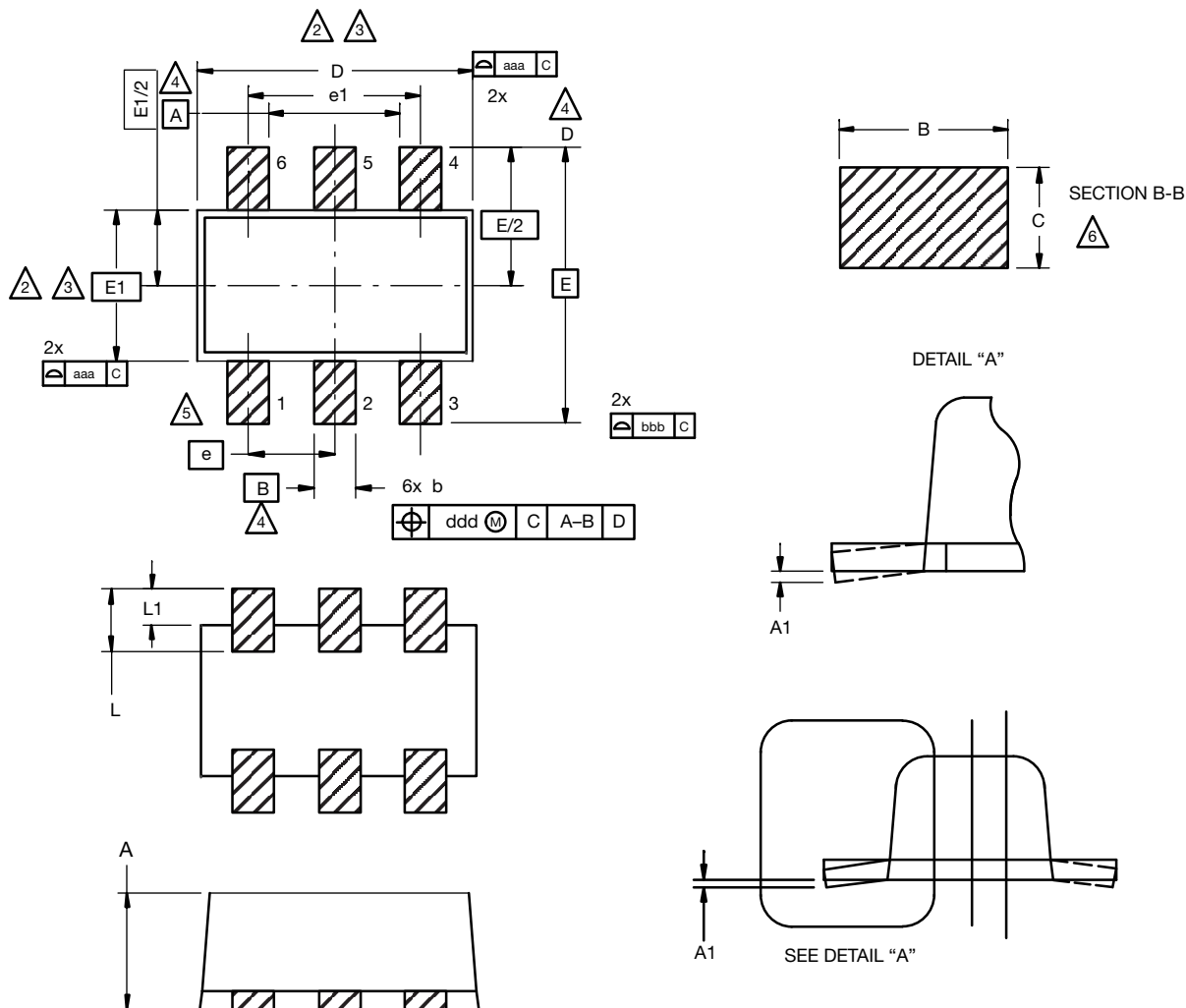
Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



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SC-89 6-Leads (SOT-563F)



Notes

1. Dimensions in millimeters.
2. Dimension D does not include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.15 mm per dimension E1 does not include interlead flash or protrusion, interlead flash or protrusion shall not exceed 0.15 mm per side.
3. Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, the bar burrs, gate burrs and interlead flash, but including any mismatch between the top and the bottom of the plastic body.
4. Datums A, B and D to be determined 0.10 mm from the lead tip.
5. Terminal numbers are shown for reference only.
6. These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.56	0.58	0.60
A1	0	0.02	0.10
b	0.15	0.22	0.30
c	0.10	0.14	0.18
D	1.50	1.60	1.70
E	1.50	1.60	1.70
E1	1.15	1.20	1.25
e	0.45	0.50	0.55
e1	0.95	1.00	1.05
L	0.25	0.35	0.50
L1	0.10	0.20	0.30

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DWG: 5880

RECOMMENDED MINIMUM PADS FOR SC-89: 6-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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